

**Silicon NPN Power Transistors**

**2SD1427**

**DESCRIPTION**

- With TO-3P(H)1S package
- Built-in damper diode
- High voltage ,high speed
- Low collector saturation voltage

**APPLICATIONS**

- Designed for use in large screen color deflection circuits

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

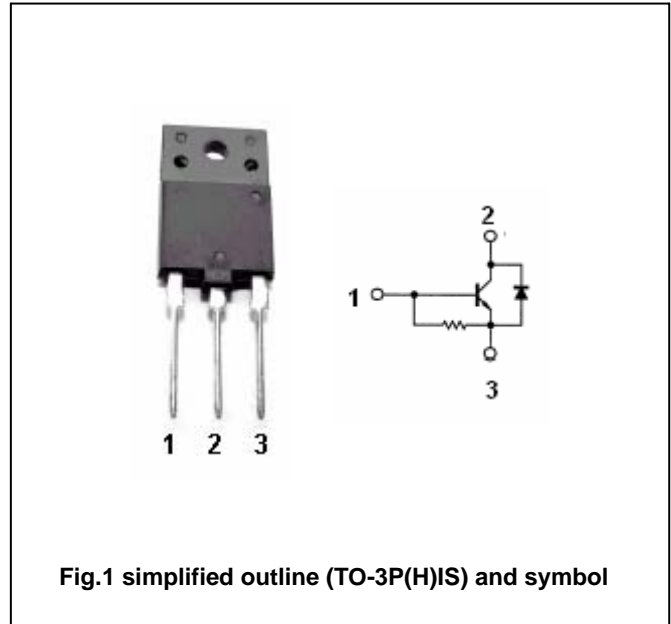


Fig.1 simplified outline (TO-3P(H)1S) and symbol

**Absolute maximum ratings (T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	600	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		5	A
I <sub>B</sub>	Base current		2.5	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25°C	80	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance junction case	1.56	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =200mA; I <sub>C</sub> =0	5			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			5.0	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =500V; I <sub>E</sub> =0			10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A; V <sub>CE</sub> =10V; f=1MHz		3		MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz		165		pF
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =5A			2.0	V
t <sub>f</sub>	Fall time	I <sub>C</sub> =4A; I <sub>B1</sub> =0.8A			1.0	μ s

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PACKAGE OUTLINE

